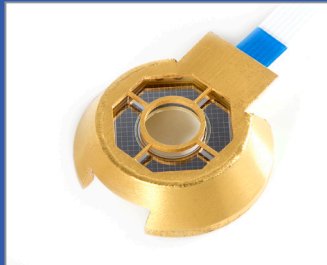
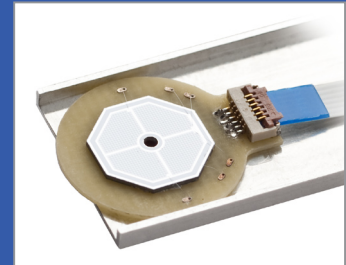


Solid State Backscattered Electron Detector

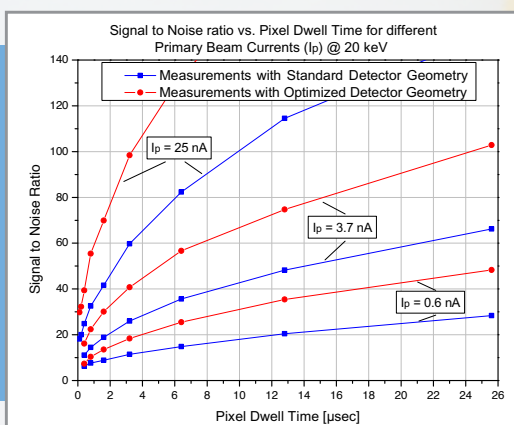
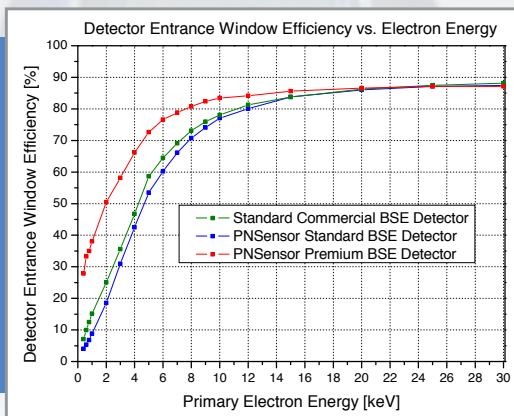
4 Quadrant Annular Detector for High Bandwidth and Low Energy Applications



50 mm² Chip mounted in pole piece configuration



40 mm² Chip mounted on retractable holder



Technical Specifications

- ▶ 4-element detector device with 40 mm² or 50 mm² active area
- ▶ Flat assembly designs, enabling working distances down to 2.5 mm
- ▶ Ø 5.6 mm or Ø 1.0 mm central hole
- ▶ Non-magnetic assembly materials with low outgassing
- ▶ Custom designed detector and housing designs for SEM integration
- ▶ Thin detector entrance window optimized for energies below 10 keV. Quantum Efficiency > 45 % @ 2 keV
- ▶ Signal capacitance < 3 pF @ full depletion for pixel dwell times < 100 ns (TV-Speed)
- ▶ Detector leakage current < 300 pA / cm² @ RT and full depletion
- ▶ Higher Signal to Noise ratios with optimized detector geometry
- ▶ Preamplifier Electronics for integration into the SEM available

PNDetector GmbH

Emil-Nolde-Str. 10 · 81735 München

Phone +49 89 309087-100

Fax +49 89 309087-277

info@pndetector.de